

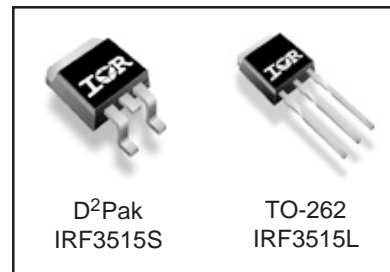
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High speed power switching

V_{DSS}	R_{DS(on) max}	I_D
150V	0.045Ω	41A

Benefits

- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective Coss Specified (See AN 1001)



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	41	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	29	
I _{DM}	Pulsed Drain Current ①	164	
P _D @ T _C = 25°C	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	4.3	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Applicable Off Line SMPS Topologies

- Telcom 48V input DC/DC Active Clamp Reset Forward Converter

Notes ① through ⑤ are on page 10

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.21	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.045	Ω	$V_{GS} = 10V, I_D = 25A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	4.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	15	—	—	S	$V_{DS} = 50V, I_D = 25A$
Q_g	Total Gate Charge	—	—	107	nC	$I_D = 25A$ $V_{DS} = 120V$ $V_{GS} = 10V$, See Fig. 6 and 13 ④
Q_{gs}	Gate-to-Source Charge	—	—	23		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	65		
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 75V$ $I_D = 25A$ $R_G = 2.5\Omega$ $R_D = 3.0\Omega$, See Fig. 10 ④
t_r	Rise Time	—	120	—		
$t_{d(off)}$	Turn-Off Delay Time	—	34	—		
t_f	Fall Time	—	63	—		
C_{iss}	Input Capacitance	—	2260	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5
C_{oss}	Output Capacitance	—	530	—		
C_{riss}	Reverse Transfer Capacitance	—	170	—		
C_{oss}	Output Capacitance	—	3330	—		
C_{oss}	Output Capacitance	—	230	—		
$C_{oss\text{ eff.}}$	Effective Output Capacitance	—	280	—		

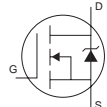
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	670	mJ
I_{AR}	Avalanche Current①	—	25	A
E_{AR}	Repetitive Avalanche Energy①	—	20	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)*	—	40	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	41	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	164		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 25A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	200	300	ns	$T_J = 25^\circ\text{C}, I_F = 25A$
Q_{rr}	Reverse Recovery Charge	—	1.6	2.4	μC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

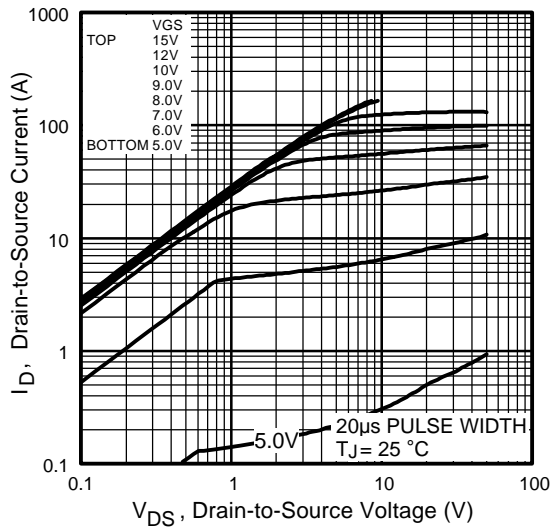


Fig 1. Typical Output Characteristics

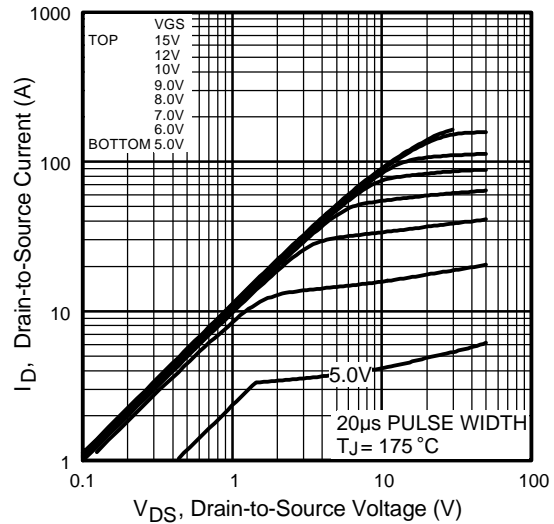


Fig 2. Typical Output Characteristics

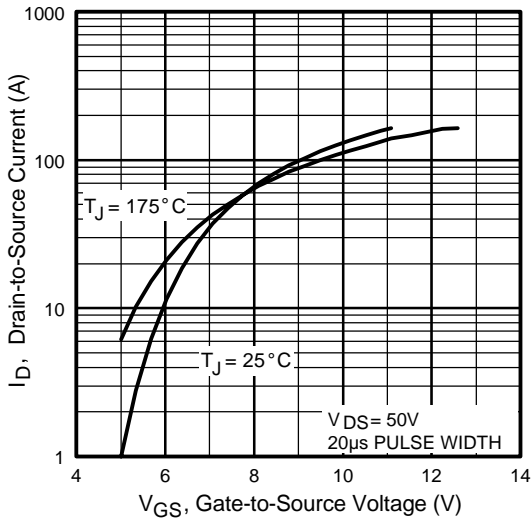


Fig 3. Typical Transfer Characteristics

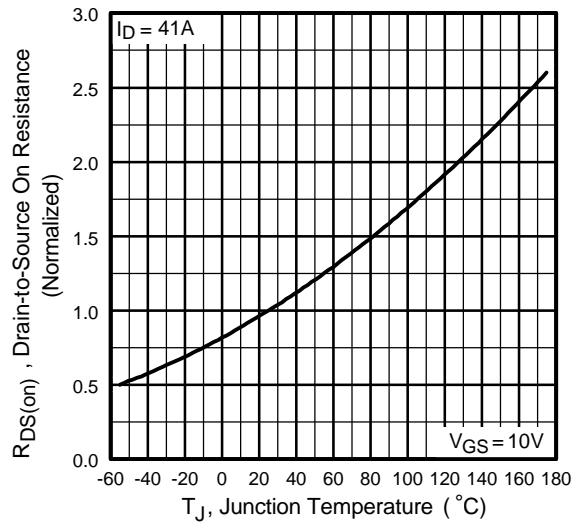


Fig 4. Normalized On-Resistance Vs. Temperature

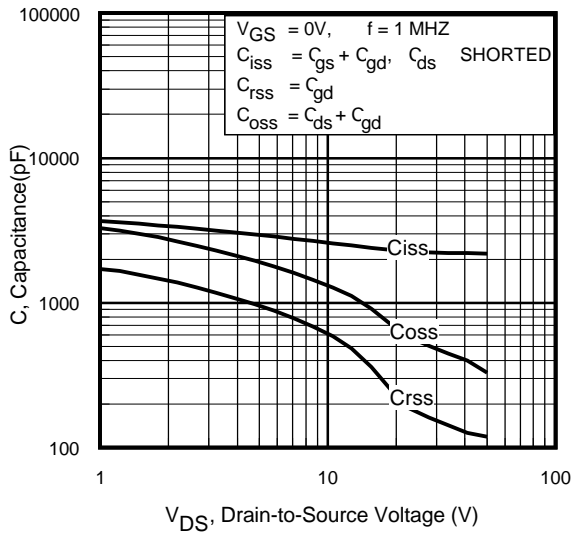


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

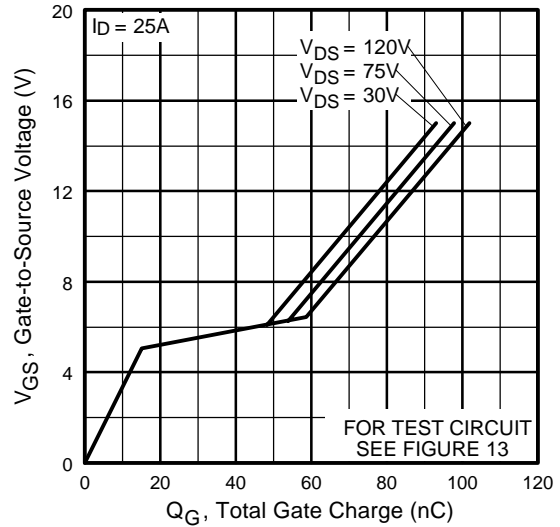


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

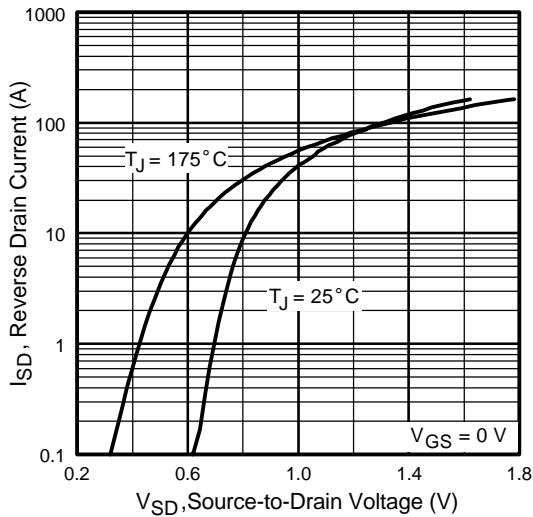


Fig 7. Typical Source-Drain Diode Forward Voltage

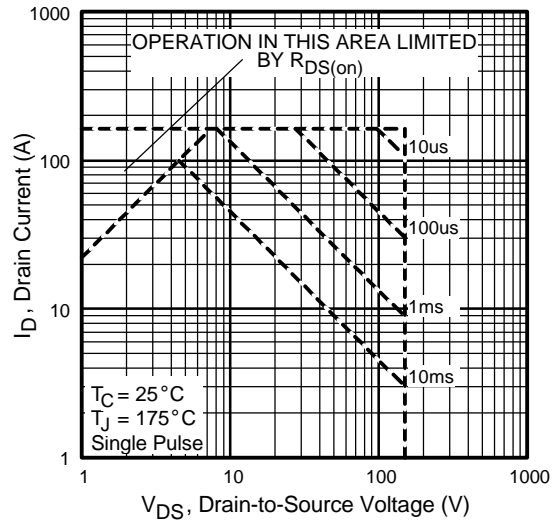


Fig 8. Maximum Safe Operating Area

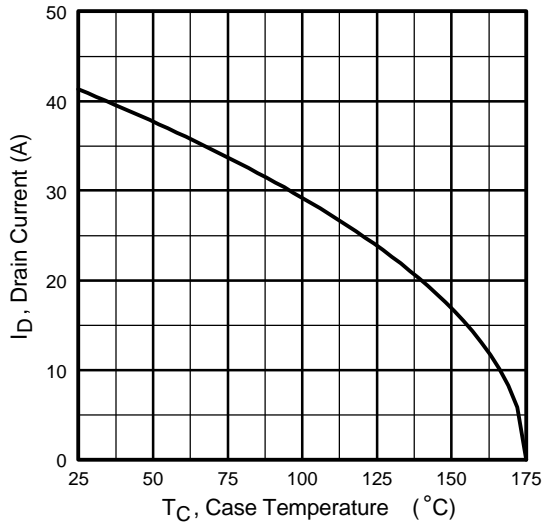


Fig 9. Maximum Drain Current Vs. Case Temperature

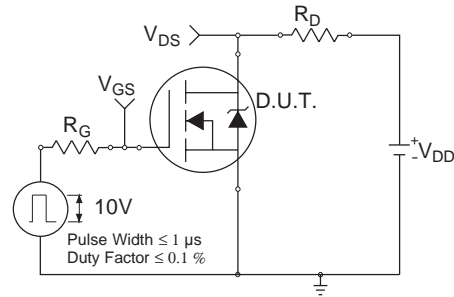


Fig 10a. Switching Time Test Circuit

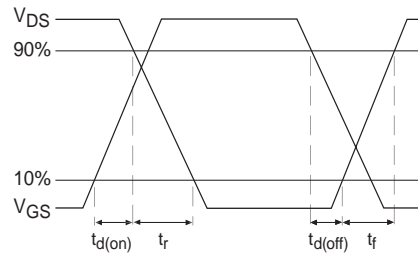


Fig 10b. Switching Time Waveforms

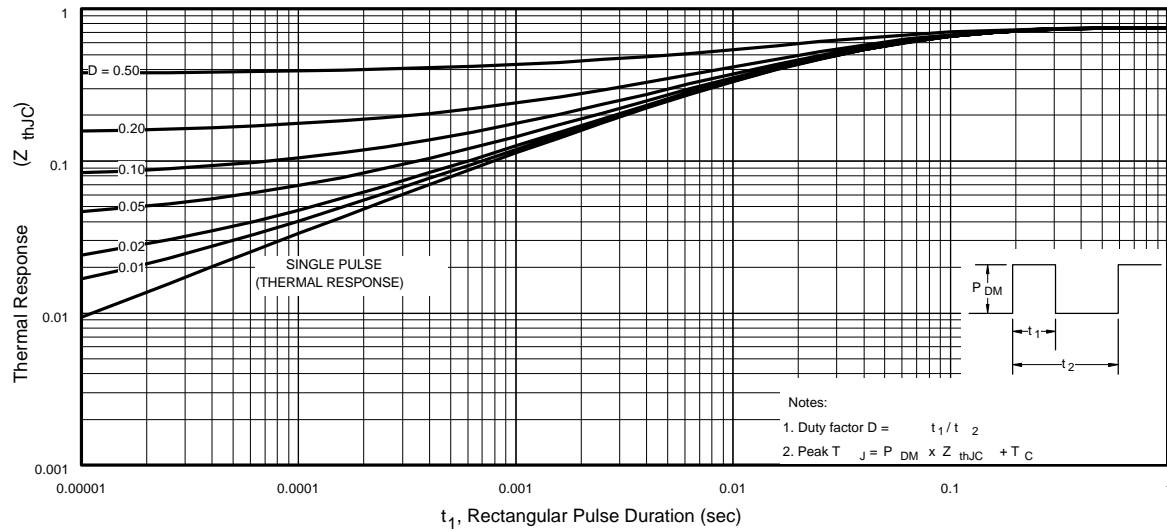


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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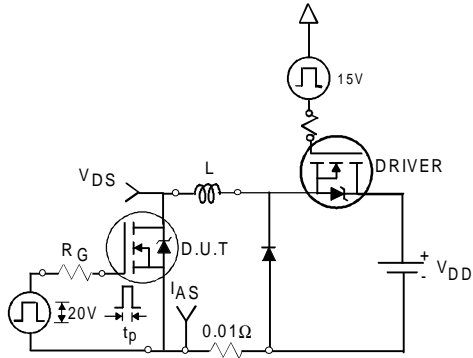


Fig 12a. Unclamped Inductive Test Circuit

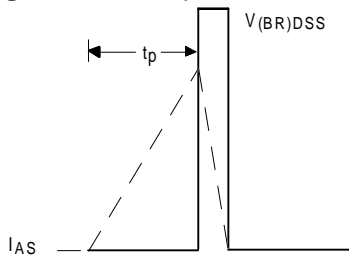


Fig 12b. Unclamped Inductive Waveforms

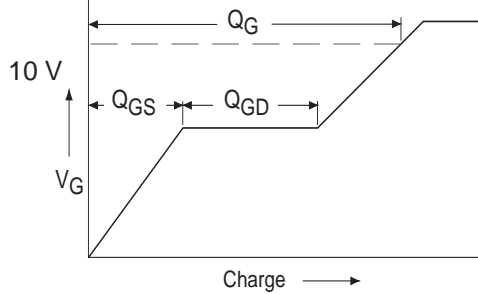


Fig 13a. Basic Gate Charge Waveform

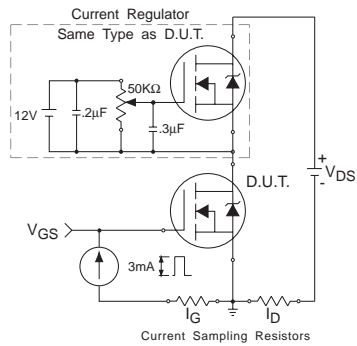


Fig 13b. Gate Charge Test Circuit

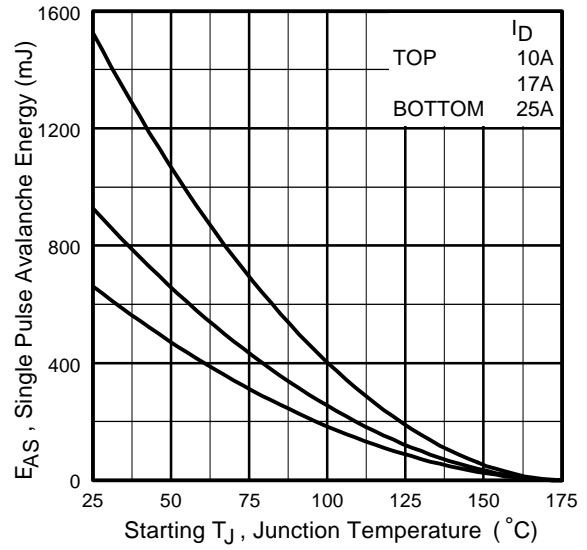
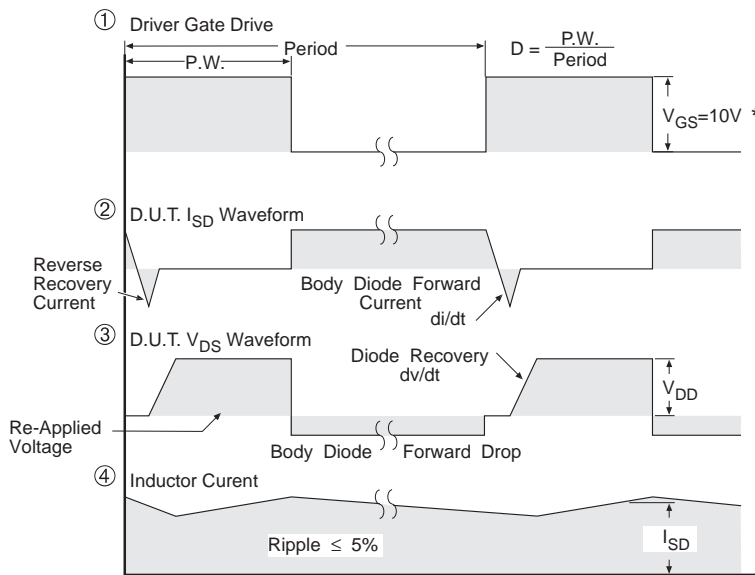
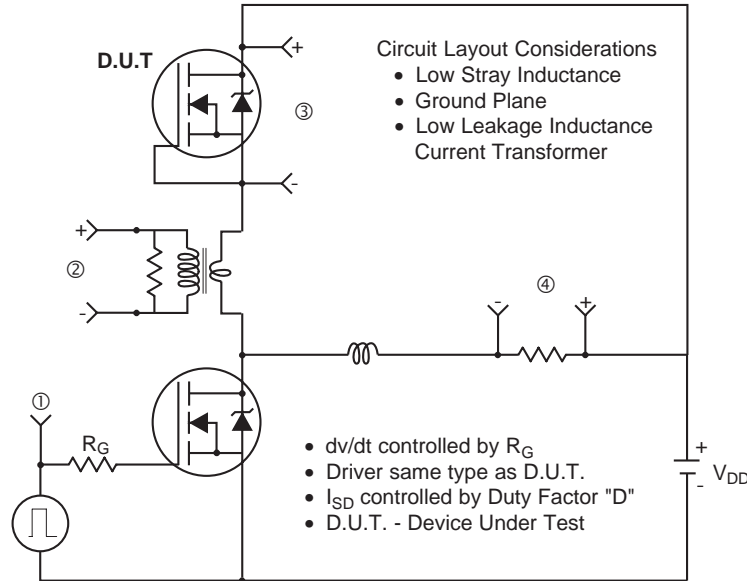


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Peak Diode Recovery dv/dt Test Circuit



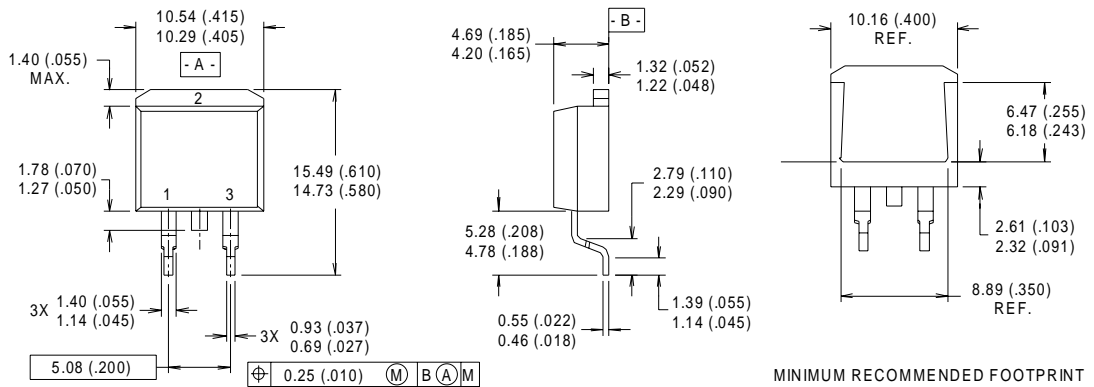
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETS

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D²Pak Package Outline



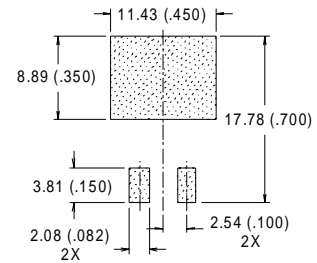
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

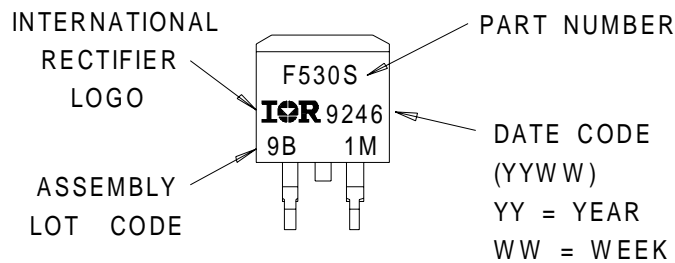
LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

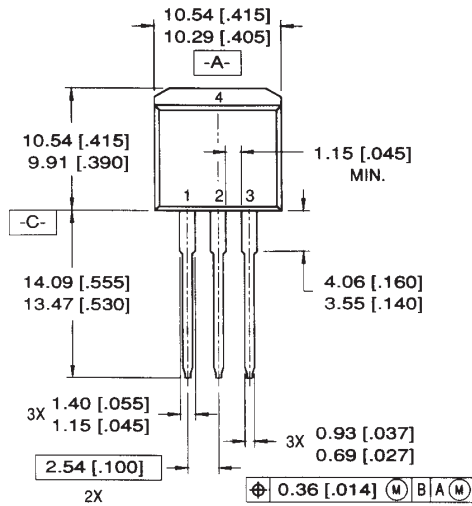
MINIMUM RECOMMENDED FOOTPRINT



D²Pak Part Marking Information

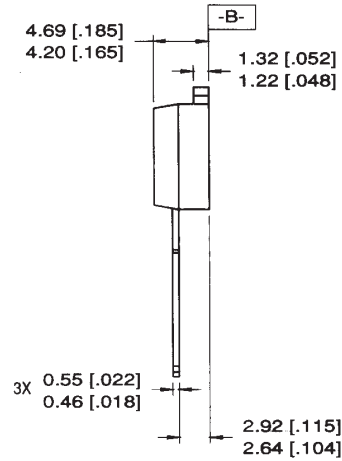


TO-262 Package Outline



LEAD ASSIGNMENTS

1 = GATE	3 = SOURCE
2 = DRAIN	4 = DRAIN

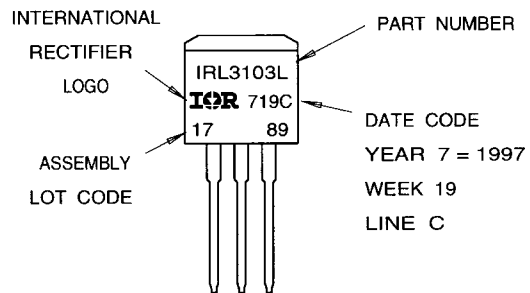


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

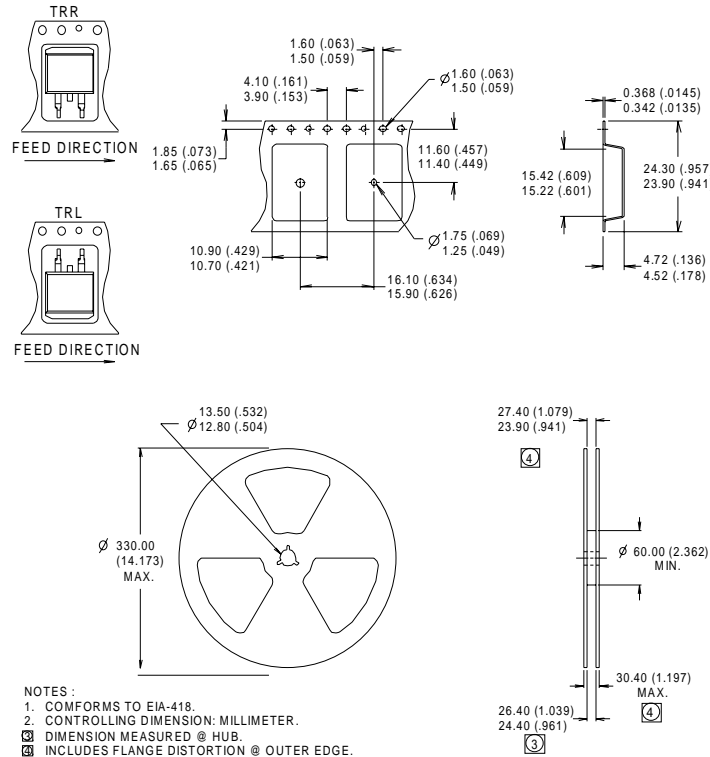
EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"



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D²Pak Tape & Reel Information



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 2.2\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 25\text{A}$. (See Figure 12)
- ③ $I_{SD} \leq 5.0\text{A}$, $di/dt \leq 330\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS}

* When mounted on FR-4 board using minimum recommended footprint.

For recommended footprint and soldering techniques refer to application note #AN-994.

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Data and specifications subject to change without notice. 10/99

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>